REMARKS

The Office Action dated June 20, 2003, has been received and carefully noted. The amendments made herein and the following remarks are submitted as a full and complete response thereto.

As a preliminary matter, Applicants appreciate the indication of allowable subject matter in claims 26, 28, 29 and 65 of the present application. Applicants also appreciate the allowance of claims 18 and 19.

Claims 1, 5, 27, 28 and 57 have been amended. Claims 10, 17, 20, 33-38, 40-47, 50, 55 and 56 have been withdrawn from further prosecution. Applicants submit that the amendments made herein are fully supported in the specification and the drawings as originally filed, and therefore no new matter has been added. Accordingly, claims 1-9, 11-16, 18, 19, 21-32, 39, 48, 49, 51-54, and 57-65 are pending in the present application and are respectfully submitted for consideration.

Claims 1-2, 4-6, 15, 16 and 61-62 were rejected under 35 U.S.C. § 102(e) as being anticipated by Kawasaki et al. (U.S. Patent No. 6,057,561). Applicants respectfully submit that each of claims 1-2, 4-6, 15, 16 and 61-62 recites subject matter that is neither disclosed nor suggested by the cited prior art.

Claim 1 recites a semiconductor light emitting device having a substrate, and a light emitting layer forming portion disposed on the substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than said active layer. The active layer is made of a ZnO-based oxide compound semiconductor containing at least Cd.

Claim 5 recites a semiconductor light emitting device having a single crystalline substrate, and a light emitting layer forming portion disposed on the substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than the active layer. The cladding layers are made of an ZnO-based oxide compound semiconductor containing Zn or Mg and Zn.

Accordingly, at least one of the essential features of the present invention is "a light emitting layer forming portion disposed on the substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than said active layer, wherein said active layer is made of a ZnO-based oxide compound semiconductor containing at least Cd. As such, the present invention results in the advantage of having an improved semiconductor light emitting device with improved crystallinity characteristics.

It is respectfully submitted that the prior art fails to disclose or suggest the elements of the Applicants' invention as set forth in claims 1, 2, 4-6, 15, 16 and 61-62, and therefore fails to provide the advantages which are provided by the present application.

Kawasaki a ZnO thin film that is fabricated on a c-surface of a sapphire substrate through use of a laser molecular beam epitaxy (MBE) method-which is effective for epitaxial growth of an oxide thin film through control at an atomic level.

Applicants respectfully submit that each and every element recited within claims 1, 5, 61 and 62 is neither disclosed nor suggested by Kawasaki. In particular,

Applicants submit that the semiconductor light emitting device as recited in the present application is clearly distinct from that which is illustrated by the combination of the cited prior art. Specifically, it is submitted that the cited prior art fails to disclose or suggest at least the limitation of a light emitting layer forming portion disposed on the substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than said active layer, wherein said active layer is made of a ZnO-based oxide compound semiconductor containing at least Cd, with respect to claim 1; and the limitation of a light emitting layer forming portion disposed on the substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than the active layer, wherein said cladding layers are made of an ZnO-based oxide compound semiconductor containing Zn or Mg and Zn, with respect to claim 5.

It is submitted that Kawasaki merely discloses that a band gap can be varied by adding Cd in ZnO but Kawasaki does not disclose any structure of light emitting device having an active layer made of ZnO-based oxide containing at least Cd, specifically $Cd_xZn_{1-x}O$. Furthermore, Kawasaki does not show that Cd must be mixed at a ratio of 0.02 to 0.4, preferably, 0.06 to 0.3 (see line 17 to 18, page 44 of the present specification) in order to use it as an active layer as is the case of the present invention, and does not give any consideration to using a ZnO-based compound layer containing Cd for the active layer for emitting the light with wavelength of blue or longer than blue.

It is further submitted that the structure to form a light-emitting device by epitaxially growing the ZnO-based compound containing Mg on a single crystal substrate is not disclosed by Kawasaki. That is, any specific structure to make the light-emitting device is not disclosed the cited prior art. As mentioned above, a light-emitting device cannot be obtained unless ZnO-based compound layers are epitaxially grown with excellent crystallinity, and they cannot be epitaxially grown unless a substrate is a single crystalline.

Moreover, Applicants respectfully submit that Kawasaki fails to disclose or suggest a low-temperature ZnO layer between the active layer containing Cd and the upper clad layer as set forth in claims 15 and 16 of the present application.

Accordingly, Applicants submit that each and every element recited within claims 1, 5, 61 and 62 is neither disclosed nor suggested by the cited prior art, and therefore each of claims 1, 5, 61 and 62 is allowable.

As for claims 2, 4, 6, 15 and 16, it is submitted that each of claims 2, 4, 6, 15 and 16 is dependent on independent claims 1 and 5, respectively. As such, each of claims 2, 4, 6, 15 and 16 is also allowable due to its dependency on allowable claims 1 and 5, respectively.

Claim 27 was rejected under 35 U.S.C. § 102(b) as being anticipated by Tishchler (U.S. Patent No. 5,661,074). Applicants respectfully submit that claim 27 recites subject matter that is neither disclosed nor suggested by the cited prior art.

Tishchler discloses a green-blue to ultraviolet emitting laser or a green-blue to ultraviolet emitting diode with a green-blue to ultraviolet light emitting gallium nitride

material on a base structure including a silicon carbide substrate, which preferably consists of 2H--SiC, 4H--SiC, or a-axis oriented 6H--SiC.

Claim 27 has been amended to depend on independent claim 1. It is submitted that Tischler fails to disclose at least the limitation of a light emitting layer forming portion disposed on the substrate so that an active layer that emits light by electric current injection is sandwiched between n-type and p-type cladding layers made of materials having a larger band gap than said active layer, wherein said active layer is made of a ZnO-based oxide compound semiconductor containing at least Cd, which is deficient from Kawasaki. Since claim 27 has been amended to depend on independent claim 1, it is submitted that claim 27 is also allowable due to its dependency on allowable claim 1.

Claims 3, 7-8, 11-13, 21-25, 52, 60 and 64 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawasaki in view of Rennie et al. (U.S. Patent No. 5,889,295, hereinafter "Rennie"). Applicants respectfully submit that each of claims 3, 7-8, 11-13, 21-25, 52, 60 and 64 recites subject matter that is neither disclosed nor suggested by the cited prior art.

Claim 13 recites a semiconductor laser having an active layer that emits light by electric current injection, and n-type and p-type cladding layers made of materials having a larger band gap than the active layer and sandwiching the active layer from both sides thereof. The active layer is made of a quantum well structure constructed with a composition modification of $Cd_xZn_{1-x}O$ ($0 \leq x < 1$), and a stress-alleviating layer is disposed on at least one side of said n-type cladding layer side and the p-type cladding layer side of the active layer so as to be in contact with the active layer. The stress-

alleviating layer being made of $Mg_wZn_{1-x}O$ ($0 \leq w < 1$) having a composition with approximately the same lattice constant as the composition located on the outermost side of the active layer on the at least one side.

Claim 21 recites a semiconductor light emitting device having a substrate, and a semiconductor laminate section disposed on the substrate and made of oxide compound semiconductor layers and including a light emitting layer forming portion. An oxide thin film containing Zn is disposed as a buffer layer on a front surface of the substrate at a lower temperature than a temperature of growing semiconductor layers of the semiconductor laminate section and is interposed between the substrate and the semiconductor laminate section.

Claim 23 recites a method of manufacturing a semiconductor light emitting device having the steps of forming a non-crystalline or polycrystalline oxide thin film containing Zn on a substrate by a sputtering method, a vacuum vapor deposition method, or a laser ablation method, putting said substrate into an apparatus for epitaxial growth of semiconductor layers and raising a substrate temperature to a growth temperature, and laminating an oxide compound semiconductor layer to form a light emitting layer forming portion.

Claim 24 recites a semiconductor light emitting device having a substrate, and a semiconductor laminate section including a light emitting layer forming portion made of compound semiconductor layers disposed on the substrate and having n-type and p-type layers to form a light emitting layer. A buffer layer is disposed between the substrate and the semiconductor laminate section, the buffer layer being made of a material having a thermal expansion coefficient larger than the thermal expansion

coefficient of an epitaxial growth layer at the lowermost layer of the semiconductor laminate section and smaller than the thermal expansion coefficient of the substrate.

Claim 60 recites a semiconductor light emitting device having a substrate, and a light emitting layer forming portion disposed on the substrate and forming a light emitting layer by lamination of compound semiconductor layers having at least an n-type layer and a p-type layer. The n-type layer is made of a ZnO-based compound semiconductor, and the p-type layer is made of a GaN-based compound semiconductor.

Rennie discloses a long-life GaN-based semiconductor device which is achieved by reducing the operating voltage of the semiconductor device having a GaN-based or a ZnSe-based compound semiconductor formed on a sapphire substrate, and by preventing the electromigration of metal atoms from an electrode into compound semiconductor layers.

Applicants submit that each of claims 3, 7, 8, 11 and 12 is dependent on independent claims 1 and/or 5, respectively. It is submitted that Rennie fails to disclose or suggest at least the deficient limitations as set forth above with respect to claims 1 and 5. Accordingly, it is further submitted that each of claims 3, 7, 8, 11 and 12 is also allowable due to its dependency on allowable claims 1 and/or 5, respectively.

As for the rejection with respect to claims 13, 21, 23, 24 52, 60 and 64, Applicants respectfully submit that each and every element recited within these claims is neither disclosed nor suggested by Kawasaki and/or Rennie, taken alone or in combination. Specifically, it is submitted that the cited prior art fails to disclose or suggest at least the limitation of "a stress-alleviating layer is disposed on at least one

side of said n-type cladding layer side and said p-type cladding layer side of said active layer so as to be in contact with said active layer, said stress-alleviating layer being made of $Mg_wZn_{1-x}O$ ($0 \leq w < 1$) having a composition with approximately the same lattice constant as the composition located on the outermost side of said active layer on said at least one side" with respect to claim 13; and the limitation of "an oxide thin film containing Zn is disposed as a buffer layer on a front surface of said substrate at a lower temperature than a temperature of growing semiconductor layers of said semiconductor laminate section and is interposed between said substrate and said semiconductor laminate section" with respect to claim 21; and the step of "laminating an oxide compound semiconductor layer to form a light emitting layer forming portion" with respect to claim 23; and the limitation of "a buffer layer is disposed between said substrate and said semiconductor laminate section, said buffer layer being made of a material having a thermal expansion coefficient larger than the thermal expansion coefficient of an epitaxial growth layer at the lowermost layer of said semiconductor laminate section and smaller than the thermal expansion coefficient of said substrate" with respect to claim 24; and the limitation of "a light emitting layer forming portion disposed on said substrate and forming a light emitting layer by lamination of compound semiconductor layers having at least an n-type layer and a p-type layer, wherein said n-type layer is made of a ZnO-based compound semiconductor, and wherein said p-type layer is made of a GaN-based compound semiconductor" with respect to claim 60.

Accordingly, Applicants submit that neither Kawasaki and/or Rennie disclose or suggest each and every element recited in claims 13, 21, 23, 24 and 60 of the present application, and therefore each of claims 13, 21, 23, 24 and 60 is allowable.

As for claims 22, 25, it is submitted that each of claims 22 and 25 is dependent on independent claims 21 and 24, respectively. As such, each of claims 22 and 25 is also allowable due to its dependency on allowable claims 21 and 24, respectively.

Claims 9, 48, 49 and 57 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawasaki. Applicants respectfully submit that each of claims 9, 48, 49 and 57 recites subject matter that is neither disclosed nor suggested by the cited prior art.

Claim 9 recites a semiconductor laser having an active layer that emits light by electric current injection, and n-type and p-type cladding layers made of materials having a larger band gap than the active layer and sandwiching the active layer from both sides thereof. The active layer is made of $Cd_xZn_{l-x}O$ ($0 \leq x < 1$), the cladding layers are made of $Mg_yZn_{1-y}O$ ($0 \leq y < 1$), and an internal electric current constriction layer is built therein.

Claim 48 recites a ZnO-based compound semiconductor light emitting device having a substrate, and a light emitting layer forming portion that forms a light emitting layer by lamination of a ZnO-based compound semiconductor layer disposed on the substrate. The ZnO-based compound semiconductor layer contains C element.

Claim 57 recites an oxide compound semiconductor light emitting diode having an n-type layer made of an n-type Zn0-based compound semiconductor, an i-layer

made of a semi-insulating ZnO-based compound semiconductor, and an electrically conductive layer disposed on a front surface of said i-layer.

Applicants respectfully submit that each and every element recited within claims 9, 48 and 57 is neither disclosed nor suggested by Kawasaki. In particular, Applicants submit that the semiconductor laser, the ZnO-based compound semiconductor light emitting device, and an oxide compound semiconductor light emitting diode as recited in the present application is clearly distinct from that which is illustrated by the combination of the cited prior art. Specifically, it is submitted that the cited prior art fails to disclose or suggest at least the limitation of "active layer is made of $Cd_xZn_{1-x}O$ ($0 \leq x < 1$), the cladding layers are made of $Mg_yZn_{1-y}O$ ($0 \leq y < 1$), and an internal electric current constriction layer is built therein" with respect to claim 9; the limitation of "and a light emitting layer forming portion that forms a light emitting layer by lamination of a ZnO-based compound semiconductor layer disposed on the substrate, wherein said ZnO-based compound semiconductor layer contains C element" with respect to claim 48; and the limitation of "an n-type layer made of an n-type Zn0-based compound semiconductor, an i-layer made of a semi-insulating ZnO-based compound semiconductor, and an electrically conductive layer disposed on a front surface of said i-layer" with respect to claim 57. Accordingly, Applicants submit that Kawasaki fails to disclose or suggest each and every element recited within claims 9, 48, and 57 of the present application, and therefore each of claims 9, 48 and 57 is allowable.

As for claim 49, it is submitted that claim 49 is dependent on independent claim 48. As such, claim 49 is also allowable due to its dependency on allowable claim 48.

Claims 14, 39, 51, 53, 54, 58 and 59 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawasaki in view of Rennie and further in view of Okazaki et al. (U.S. Patent No. 5,966,396, hereinafter "Okazaki"). Applicants respectfully submit that each of claims 14, 39, 51, 53, 54, 58 and 59 recites subject matter that is neither disclosed nor suggested by the cited prior art.

Claim 39 recites a semiconductor light emitting device having a substrate, and a light emitting layer forming portion made of ZnO-based compound semiconductor layers disposed on the substrate and forming a light emitting layer with an n-type layer and a p-type layer. The p-type layer contains an element capable of becoming an n-type dopant as a buffering agent.

Claim 51 recites a semiconductor laser having a substrate, a first cladding layer disposed on said substrate and made of a first conductivity type semiconductor, an active layer disposed on said first cladding layer, and a second cladding layer disposed on the active layer and made of a second conductivity type semiconductor. In addition, the semiconductor laser includes an electric current constriction layer disposed in the inside of or in the vicinity of said second cladding layer. The electric current constriction layer is made of a ZnO-based compound semiconductor doped with a Group IA or Group VB element.

Claim 54 recites a semiconductor laser comprising a substrate, a first cladding layer disposed on the substrate and made of a first conductivity type semiconductor, an active layer disposed on said first cladding layer, a second cladding layer disposed on said active layer and made of a second conductivity type semiconductor, and an electric current constriction layer disposed in the inside of or in the vicinity of said

second cladding layer and made of $Mg_zZn_{1-z}O$ ($0 \leq z < 1$). An etching stopping layer made of $Cd_sZn_{1-s}O$ ($0 < s < 1$) or $Be_tZn_{1-t}O$ ($0 < t < 1$) is disposed on said substrate side of said electric current constriction layer.

Claim 58 recites an oxide compound semiconductor light emitting diode having an n-type layer made of an n-type ZnO-based compound semiconductor, a doped layer in which a ZnO-based compound semiconductor layer is doped with at least one kind of element selected from the group consisting of Group IA, Group IB, and Group VB elements, and an electrically conductive layer disposed on a front surface of the doped layer.

Okazaki discloses a semiconductor laser that is formed from a gallium nitride-based compound semiconductor material, and has a double-heterostructure portion obtained by sandwiching an active layer between an n-type cladding layer and a p-type cladding layer on a sapphire substrate.

Applicants respectfully submit that each and every element recited within claims 39, 51, 54 and 58 is neither disclosed nor suggested by Kawasaki, Rennie, and/or Okazaki, taken alone or in combination. In particular, Applicants submit that the semiconductor light emitting device, the semiconductor laser, and the oxide compound semiconductor light emitting diode as recited in the present application is clearly distinct from that which is illustrated by the combination of the cited prior art. Specifically, it is submitted that the cited prior art fails to disclose or suggest at least the limitation of "a light emitting layer forming portion made of ZnO-based compound semiconductor layers disposed on said substrate and forming a light emitting layer with an n-type layer and a p-type layer, wherein said p-type layer contains an element

capable of becoming an n-type dopant as a buffering agent" with respect to claim 39; at least the limitation of the "electric current constriction layer is made of a ZnO-based compound semiconductor doped with a Group IA or Group VB element" with respect to claim 51; at least the limitation of "a doped layer in which a ZnO-based compound semiconductor layer is doped with at least one kind of element selected from the group consisting of Group IA, Group IB, and Group VB elements, and an electrically conductive layer disposed on a front surface of said doped layer" with respect to claim 58; and at least the limitation of "a light emitting layer forming portion disposed on said substrate and forming a light emitting layer by lamination of compound semiconductor layers having at least an n-type layer and a p-type layer, wherein said n-type layer is made of a ZnO-based compound semiconductor, and wherein said p-type layer is made of a GaN-based compound semiconductor" with respect to claim 60.

Applicants submit that the p-layer of the present invention becomes insulated even when the p-dopant is added in order to form the p-layer, and the n-dopant is added to increase the functions as the p-dopant by combining both the dopants, and therefore the p-type is thereby obtained. Consequently, it is submitted that n-dopant is contained in the p-type layer of the present invention, and neither Kawasaki, Rennie, nor Okazaki discloses or suggest such feature.

Furthermore, with respect to claims 51 and 58, the Applicants disagree with the Examiner's position that Okazaki discloses a current blocking layer and it is obvious to use Group I to form the p-type in the ZnO-based compound. It is submitted that the current blocking layer of Okazaki cannot block the current unless it is made by a conductivity type different from surrounding conductivity type or insulation.

Consequently, in the p-type layer of Okazaki, the current blocking layer must be formed by either the n-type or the insulation layer. In the present invention, the p-dopant is added to achieve semi-insulation and Group I elements are not added to achieve the p-type. Applicants submit that since Okazaki does not use any ZnO-based oxide, there is no motivation to combine Okazaki with the cited prior art.

With respect to claim 54, Applicants disagree with the Examiner's position that Kawasaki's n-contact layer 13 could be of CdZnO. It is submitted that Kawasaki does not disclose any etching stop layer. The present invention discloses an etching stopping layer used when a current constriction layer is etched in the form of stripes, which is located at a critical position close to the light emitting layer and does not allow either over-etching or short-etching, and for which material with an etching rate different from that of the current constriction layer must be used. It is therefore submitted that at least the above features are not obvious and are not shown in the cited prior art.

In view of the above, Applicants submit that each and every element of claims 39, 51, 54 and 58 is neither disclosed nor suggested in the cited prior art, and therefore each of claims 39, 51, 54 and 58 is allowable.

As for the rejection of claim 14, it is submitted that claim 14 is dependent on independent claim 13. As such, claim 14 is also allowable due to its dependency on allowable claim 13 for at least the reasons set forth above.

As for claims 53 and 59, it is submitted that each of claims 53 and 59 is dependent on independent claims 51 and 58, respectively. As such, each of claims 53

and 59 is also allowable due to its dependency on allowable claims 51 and 58, respectively.

Claims 30-32 and 63 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawasaki in view of McTeer (U.S. Patent No. 5,700,718). Applicants respectfully submit that each of claims 30-32 and 63 recites subject matter that is neither disclosed nor suggested by the cited prior art.

Claim 30 recites a ZnO-based compound semiconductor light emitting device having a substrate, and a light emitting layer forming portion disposed on said substrate and forming a light emitting layer by lamination of ZnO-based compound semiconductor having at least an n-type layer. An n-side electrode disposed in contact with said n-type layer of said ZnO-based compound semiconductor is formed so that a portion of said n-side electrode which is in contact with said n-type layer is formed of Ti or Cr, the portion not containing A1.

Claim 63 recites a semiconductor light emitting device having an insulating substrate, a light emitting layer forming portion formed of a p-type layer disposed on said insulating substrate and made of a GaN-based compound semiconductor and an n-type layer disposed on said p-type layer and made of a ZnO-based compound semiconductor, an n-side electrode disposed on said n-type layer, and a p-side electrode disposed on said p-type layer which is exposed by removal of a portion of said ZnO-based compound semiconductor layer through etching.

McTeer merely discloses a method for forming titanium aluminide on a passivation layer of a silicon substrate surface.

Applicants respectfully submit that each and every element recited within claims 30 and 63 is neither disclosed nor suggested by Kawasaki and/or McTeer, taken alone or in combination. In particular, Applicants submit that the ZnO-based compound semiconductor light emitting device and the semiconductor light emitting device as recited in the present application is clearly distinct from that which is illustrated by the combination of the cited prior art. Specifically, it is submitted that the cited prior art fails to disclose or suggest at least the limitation of "an n-side electrode disposed in contact with said n-type layer of said ZnO-based compound semiconductor is formed so that a portion of said n-side electrode which is in contact with said n-type layer is formed of Ti or Cr, the portion not containing A1" with respect to claim 30; and at least the limitation of "a p-side electrode disposed on said p-type layer which is exposed by removal of a portion of said ZnO-based compound semiconductor layer through etching" with respect to claim 63.

Applicants submit that McTeer does not disclose the type of metal that should be used to enable the low-resistant connection in order to achieve ohmic contact with the ZnO-based layer. The electrode material should be selected in such a manner that low-resistant contact can be obtained by a semiconductor layer to which the electrode material is equipped. As such, the electrode material suited for the ZnO-based semiconductor layer and its construction are recited in claims 30 through 32. With respect to the electrode, which is brought in contact with the ZnO-based semiconductor layer of the present invention, it is submitted that the cited prior art fails to disclose such feature.

In addition, Applicants submit that the cited prior fails to disclose at least the element of "a p-side electrode disposed on said p-type layer which is exposed by removal of a portion of said ZnO-based compound semiconductor layer through etching" as recited in claim 63. Accordingly, it is submitted that each and every element recited within claims 30 and 63 is neither disclosed nor suggested in Kawasaki and/or McTeer, taken alone or in combination, and therefore each of claims 30 and 63 is allowable.

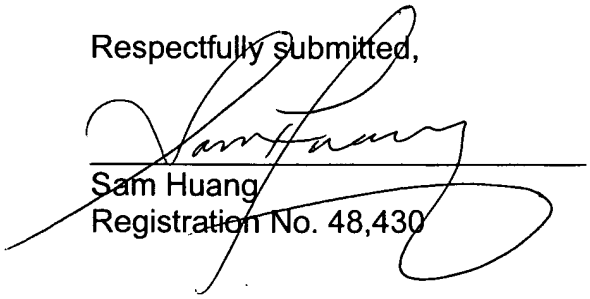
As for claims 31 and 32, it is submitted that each of claims 31 and 32 is dependent on independent claim 30. As such, each of claims 31 and 32 is also allowable due to its dependency on allowable claim 30.

In view of the above, Applicants respectfully submit that claims 1-9, 11-16, 18, 19, 21-32, 39, 48, 49, 51-54, and 57-65, each recite subject matter that is neither disclosed nor suggested in the cited prior art. Applicants also submit that the subject matter is more than sufficient to render the claims non-obvious to a person of ordinary skill in the art, and therefore respectfully request that claims 1-9, 11-16, 18, 19, 21-32, 39, 48, 49, 51-54, and 57-65 be found allowable and that this application be passed to issue.

If for any reason, the Examiner determines that the application is not now in condition for allowance, it is respectfully requested that the Examiner contact the Applicants' undersigned attorney at the indicated telephone number to arrange for an interview to expedite the disposition of this application.

In the event this paper has not been timely filed, the Applicants respectfully petition for an appropriate extension of time. Any fees for such an extension, together with any additional fees that may be due with respect to this paper, may be charged to counsel's Deposit Account No. 01-2300, **referencing docket number 107400-00023.**

Respectfully submitted,



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Enclosure: Petition for Extension of Time (one month)